

INA5006AC1

FOR HIGH CURRENT DRIVE APPLICATION
SILICON PNP EPITAXIAL TYPE

DESCRIPTION

INA5006AC1 is a silicon PNP epitaxial type transistor.
It is designed with high collector current and small $V_{CE(sat)}$.

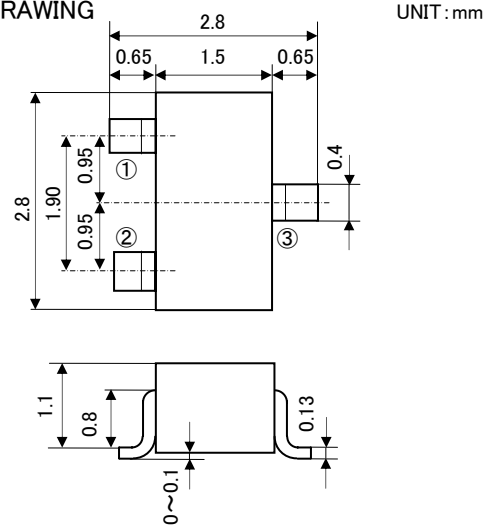
FEATURE

- Super mini package for easy mounting
- High collector current ($I_C = -2A$)
- Low collector saturation voltage
($V_{CE(sat)} < -0.2V_{max}; I_C = -1A, I_B = -33mA$)

APPLICATION

Audiovisual apparatus, Relay drive

OUTLINE DRAWING



Terminal Connector JEITA:SC-59
JEDEC: Similar to TO-236
①: Base
②: Emitter
③: Collector

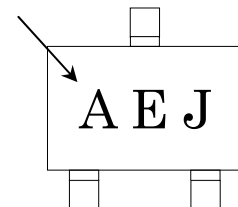
MAXIMUM RATING ($T_a = 25^\circ C$)

SYMBOL	PARAMETER	RATING	UNIT
V_{CEO}	Collector to Emitter voltage	-50	V
V_{CBO}	Collector to Base voltage	-50	V
V_{EBO}	Emitter to Base voltage	-7	V
I_C	Collector current	-2	A
P_C	Collector dissipation ($T_a = 25^\circ C$)	200	mW
		900(*)	
T_j	Junction temperature	+150	$^\circ C$
T_{stg}	Storage temperature	-55 ~ +150	$^\circ C$

*Mounted on ceramic board (19mm × 9mm × 1mm)

MARKING

Type Name



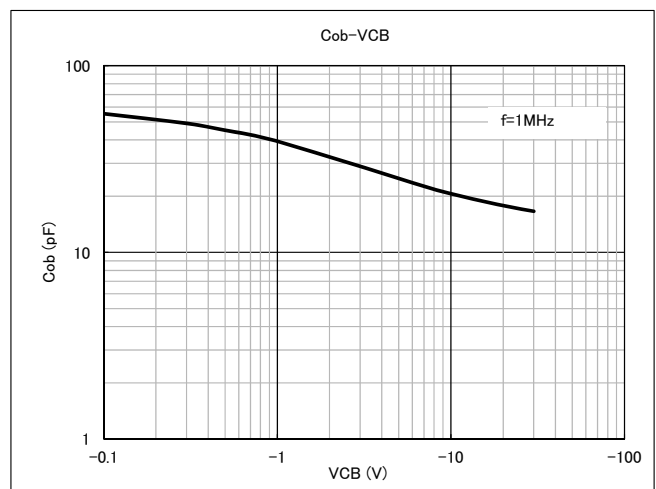
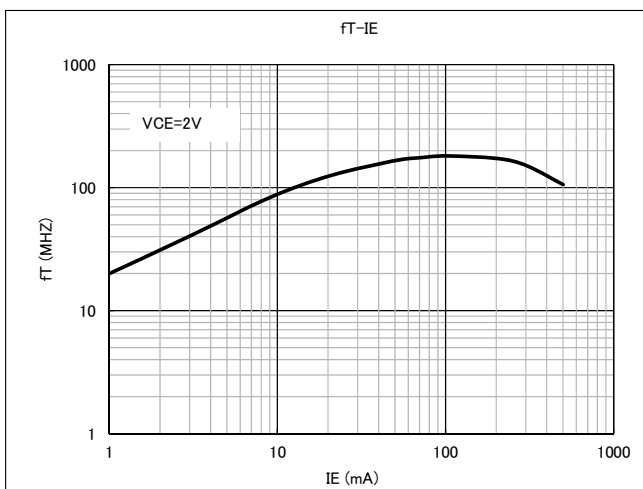
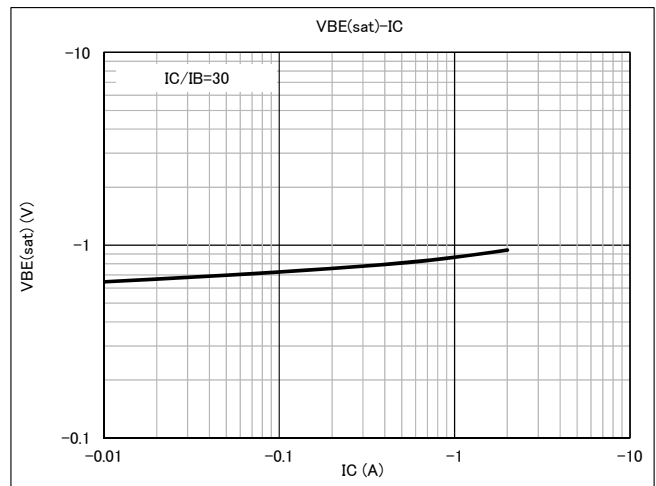
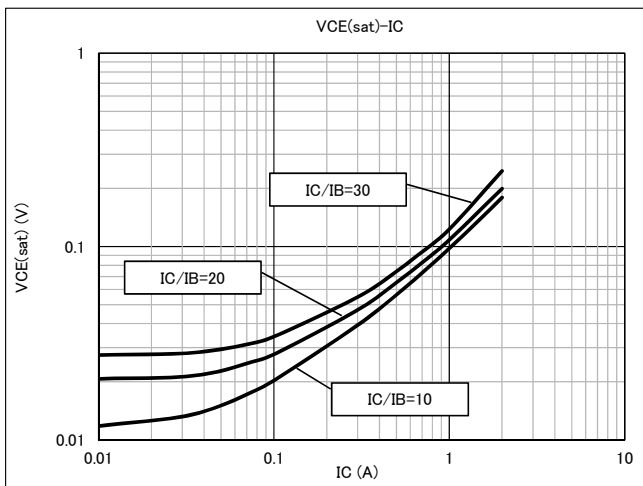
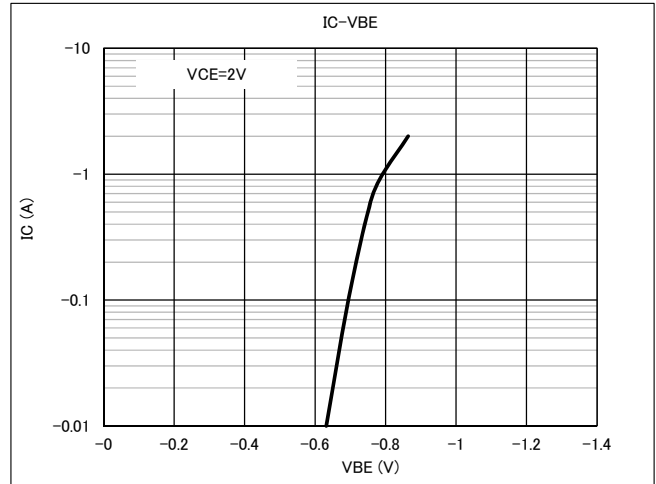
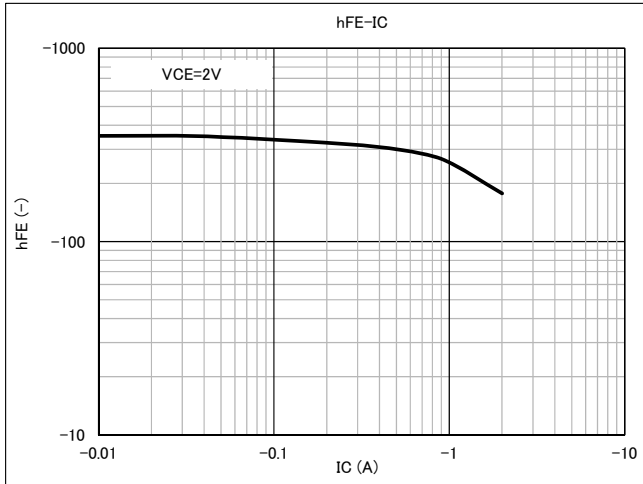
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
$V_{(BR)CEO}$	C to E break down voltage	$I_C = -10mA, I_B = 0mA$	-50	-	-	V
$V_{(BR)CBO}$	C to B break down voltage	$I_C = -100\mu A, I_E = 0mA$	-50	-	-	V
$V_{(BR)EBO}$	E to B break down voltage	$I_E = -100\mu A, I_C = 0mA$	-7	-	-	V
I_{CBO}	Collector cut off current	$V_{CB} = -50V, I_E = 0mA$	-	-	-0.1	μA
I_{EBO}	Emitter cut off current	$V_{EB} = -7V, I_C = 0mA$	-	-	-0.1	μA
h_{FE1}	DC forward current gain1	$V_{CE} = -2V, I_C = -300mA$	200	-	500	-
h_{FE2}	DC forward current gain2	$V_{CE} = -2V, I_C = -1A$	100	-	-	-
$V_{CE(sat)}$	C to E saturation voltage	$I_C = -1A, I_B = -33mA$	-	-	-0.2	V
$V_{BE(sat)}$	B to E saturation voltage	$I_C = -1A, I_B = -33mA$	-	-	-1.1	V
f_T	Gain bandwidth product	$V_{CE} = -2V, I_E = 300mA, f = 100MHz$	-	180	-	MHz
Cob	Collector output capacitance	$V_{CB} = -10V, f = 100MHz$	-	20	-	pF

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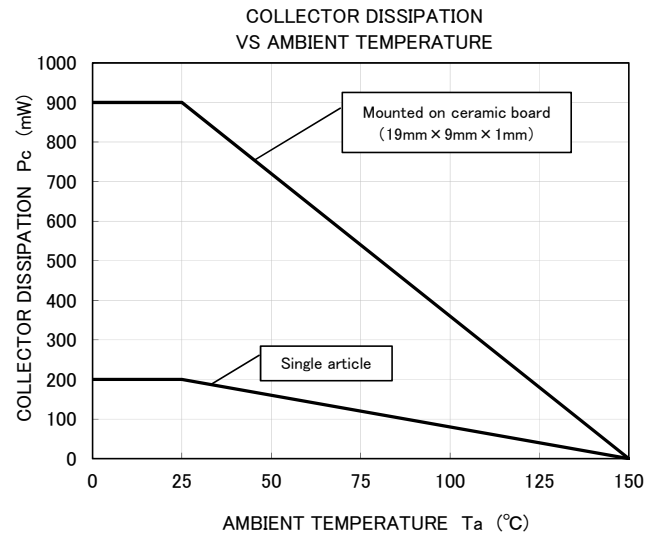
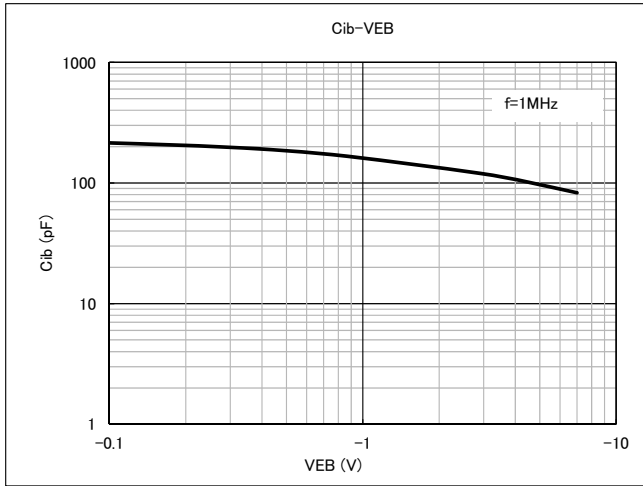
FOR HIGH CURRENT DRIVE APPLICATION
SILICON PNP EPITAXIAL TYPE

TYPICAL CHARACTERISTICS (Ta=25°C)



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SILICON PNP EPITAXIAL TYPE





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